

LEGM200BH120L2K

IGBT Power Module

Features:

- $V_{CE}=1200V$ $I_C=200A$
- Low $V_{CE(sat)}$
- V_{CEsat} with positive temperature coefficient
- Maximum junction temperature 150°C
- Isolation Type Package

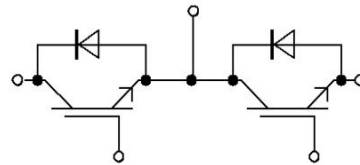
Applications:

- The inverter
- Motor control and drives

Package Type & Internal Circuit



L2



Internal Circuit

Maximum Rated Values (IGBT Inverter)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Collector-emitter voltage	$V_{EC}=0V, I_C=1mA, T_{vj}=25^\circ C$	1200	V
I_C	Continuous Collector Current	$T_C=100^\circ C$	200	A
I_{CRM}	Peak Collector Current	$I_{CRM}=2I_C$	400	A
V_{GES}	Gate-Emitter Voltage	$T_{vj}=25^\circ C$	± 30	V
P_{tot}	Total Power Dissipation	$T_C=25^\circ C, T_{vjmax}=150^\circ C$	950	W

Maximum Rated Values (IGBT Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=200\text{ A}, V_{GE}=15\text{ V}, T_{vj}=25\text{ }^\circ\text{C}$		2.10		V
		$I_C=200\text{ A}, V_{GE}=15\text{ V}, T_{vj}=125\text{ }^\circ\text{C}$		2.50		V
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=5.0\text{ mA}, V_{CE}=V_{GE}, T_{vj}=25\text{ }^\circ\text{C}$		5.8		V
I_{CES}	Collector-Emitter Cut-off Current	$V_{CE}=1200\text{ V}, V_{GE}=0\text{ V}, T_{vj}=25\text{ }^\circ\text{C}$			3.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{CE}=0\text{ V}, V_{GE}=15\text{ V}, T_{vj}=25\text{ }^\circ\text{C}$			400	nA
$t_{d(on)}$	Turn-on Delay Time, Inductive Load	$I_C=200\text{ A}, V_{CE}=600\text{ V}$ $V_{GE}=\pm 15\text{ V}$ $R_{Gon}=2\ \Omega$ $T_{vj}=25\text{ }^\circ\text{C}$		49		ns
t_r	Rise Time, Inductive Load			72		ns
$t_{d(off)}$	Turn-off Delay Time, Inductive Load			339		ns
t_f	Fall Time, Inductive Load			72		ns
E_{on}	Turn-on Energy Loss per Pulse			10.4		mJ
E_{off}	Energy Loss per Pulse			15		mJ
$t_{d(on)}$	Turn-on Delay Time, Inductive Load		$I_C=200\text{ A}, V_{CE}=600\text{ V}$ $V_{GE}=\pm 15\text{ V}$ $R_{Gon}=2\ \Omega$ $T_{vj}=125\text{ }^\circ\text{C}$		50	
t_r	Rise Time, Inductive Load			77		ns
$t_{d(off)}$	Turn-off Delay Time, Inductive Load			375		ns
t_f	Fall Time, Inductive Load			262		ns
E_{on}	Turn-on Energy Loss per Pulse			11.5		mJ
E_{off}	Energy Loss per Pulse			21		mJ
R_{thJC}	Thermal resistance, junction to case	per IGBT				0.13
$T_{vj\ op}$	Temperature under switching conditions		-40		125	$^\circ\text{C}$

Maximum Rated Values (Diode Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	$T_{vj}=25\text{ }^{\circ}\text{C}$		1200		V
I_F	Continuous DC Forward Current	$T_C=100\text{ }^{\circ}\text{C}$		200		A
I_{FRM}	Repetitive Peak Forward Current	$t_p=1\text{ ms}$		400		A
I^2t	I^2t Value	$V_R=0\text{ V}$, $t_p=10\text{ ms}$, $T_{vj}=125\text{ }^{\circ}\text{C}$		7500		A^2s

Characteristic Values (Diode Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage	$I_F=200\text{ A}$, $V_{CE}=0\text{ V}$, $T_{vj}=25\text{ }^{\circ}\text{C}$		2.15		V
		$I_F=200\text{ A}$, $V_{CE}=0\text{ V}$, $T_{vj}=125\text{ }^{\circ}\text{C}$		2.25		V
t_{rr}	Reverse Recovery time	$I_F=200\text{ A}$, $V_R=600\text{ V}$ $-di/dt=3750\text{ A/us}$		120		ns
Q_r	Recovered Charge			16.5		μC
E_{rec}	Reverse Recovery Energy		$T_{vj}=25\text{ }^{\circ}\text{C}$		9.2	
t_{rr}	Reverse Recovery time	$I_F=200\text{ A}$, $V_R=600\text{ V}$ $-di/dt=3750\text{ A/us}$		291		ns
Q_r	Recovered Charge			2.75		μC
E_{rec}	Reverse Recovery Energy		$T_{vj}=125\text{ }^{\circ}\text{C}$		15.3	
R_{thJC}	Thermal resistance, junction to case	per Diode			0.19	K/W
$T_{vj\text{ op}}$	Operating Junction Temperature		-40		125	$^{\circ}\text{C}$

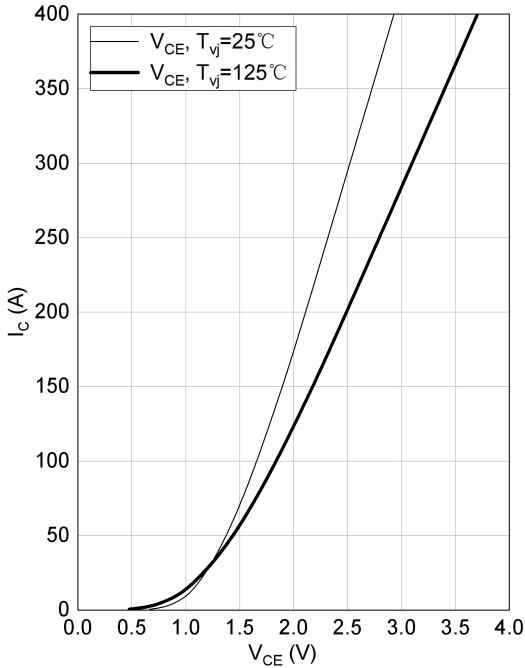
Module Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{isol}	Isolation voltage	$t=1\text{ min}$, $f=50\text{ Hz}$	2500			V
T_{stg}	Storage Temperature		-40		125	$^{\circ}\text{C}$
M_t	Module Electrodes Torque	Recommended(M6)	2.5		5.0	N·m
M_s	Module-to-Sink Torque	Recommended(M6)	3.0		6.0	N·m
G	Weight of Module			300		g

Output characteristic of IGBT, Inverter (typical)

$$I_c = f(V_{CE})$$

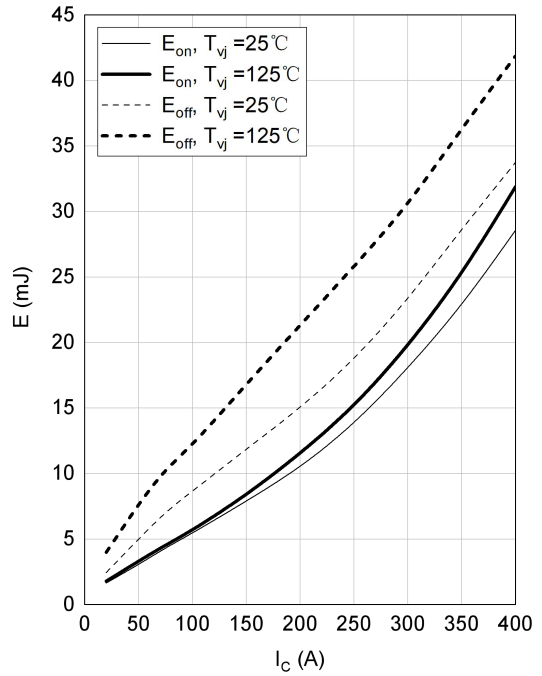
$$V_{GE} = 15V$$



Switching time of IGBT, Inverter (typical)

$$E_{on} = f(I_c), E_{off} = f(I_c)$$

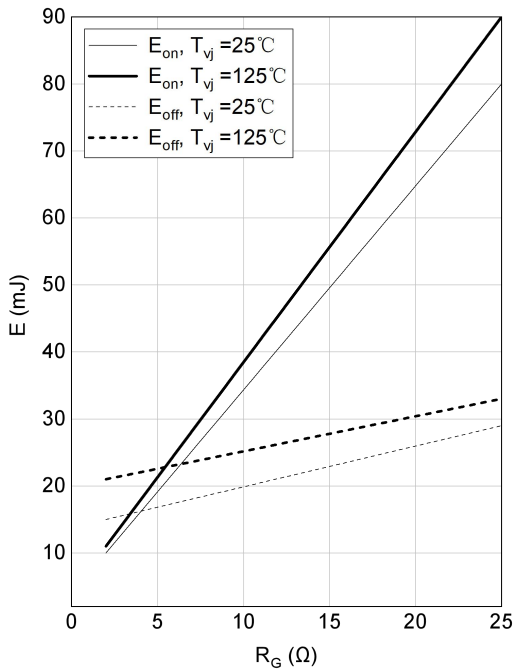
$$V_{GE} = \pm 15V, R_G = 2\Omega, V_{CE} = 600V$$



Switching losses of IGBT, Inverter (typical)

$$E_{on} = f(R_G), E_{off} = f(R_G)$$

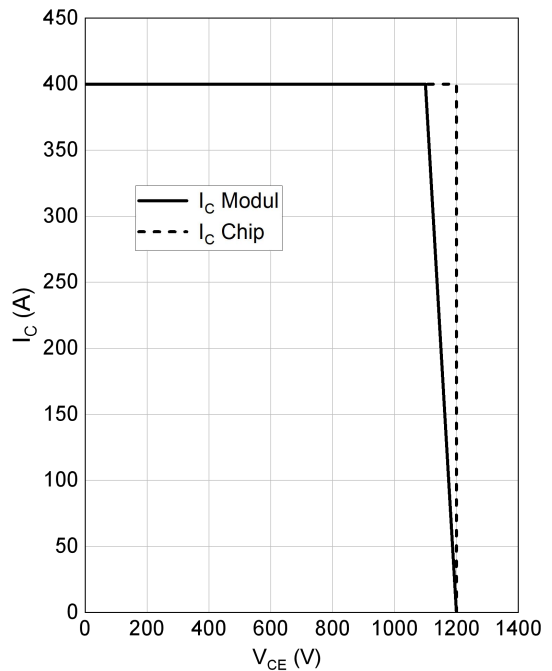
$$V_{GE} = \pm 15V, I_c = 200A, V_{CE} = 600V$$



RBSOA IGBT, Inverter (typical)

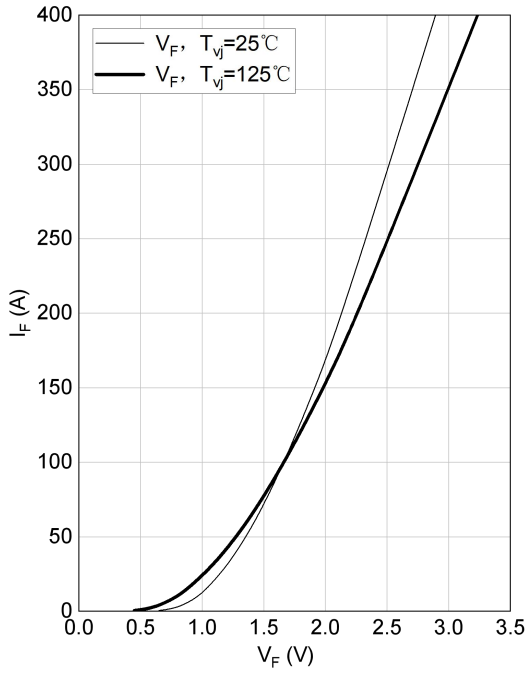
$$I_c = f(V_{CE})$$

$$V_{GE} = \pm 15V, R_{Goff} = 2\Omega, T_{vj} = 125^\circ C$$



Forward characteristic of Diode, Inverter (typical)

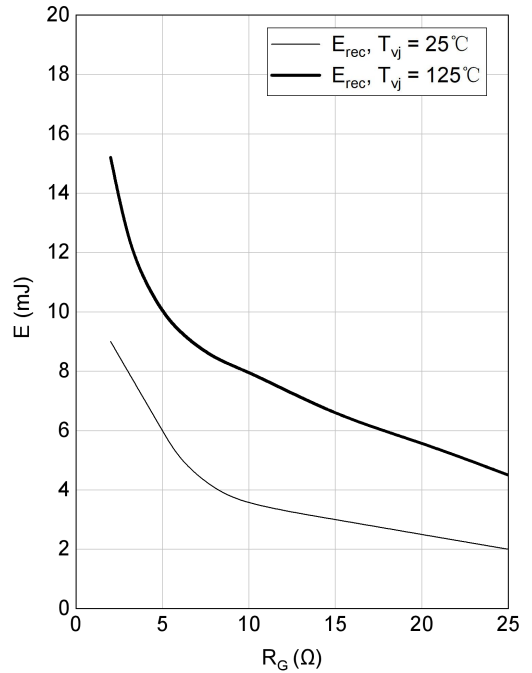
$$I_F = f(V_F)$$



Switching losses of Diode, Inverter (typical)

$$E_{rec} = f(R_G)$$

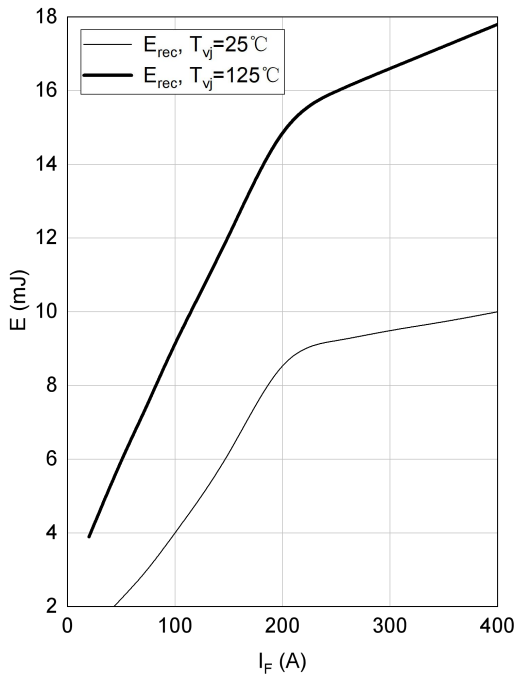
$I_F = 200A, V_{CE} = 600V$



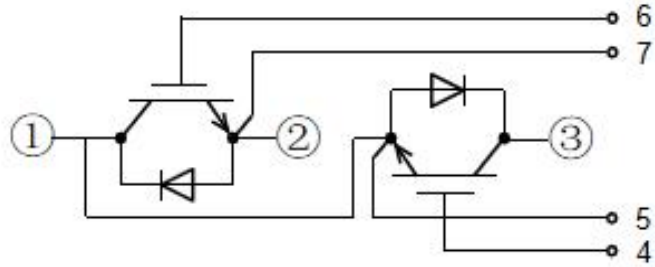
Switching losses of Diode, Inverter (typical)

$$E_{rec} = f(I_F)$$

$R_{Gon} = 2\Omega, V_{CE} = 600V$

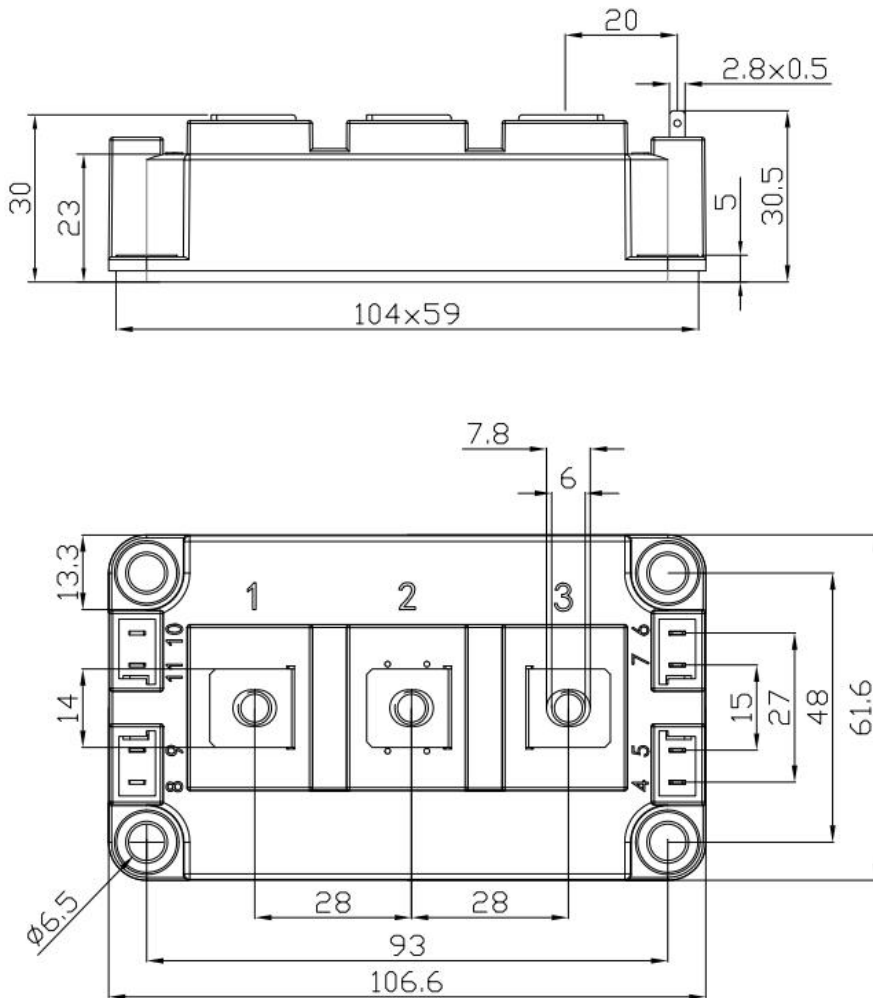


Circuit Diagram



Package Dimensions

(Dimensions in Millimeters)



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